**Product data sheet** 

## 1. General description

Dual common cathode power Schottky diode designed for high frequency switched mode power supplies in a TO-220 plastic package.

### 2. Features and benefits

- Trench structure
- · High junction temperature up to 150°C
- · High efficiency
- Low forward voltage drop, negligible switching losses

## 3. Applications

- · DC to DC converters
- Freewheeling diode
- · OR-ing diode

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	-	100	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 133 °C; square-wave pulse; per diode; Fig. 1; Fig. 2; Fig. 3	-	-	20	Α
I <sub>O(AV)</sub>	average output current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 130 °C; square-wave pulse; both diodes conducting	-	-	40	Α
Static charac	cteristics					
$V_{F}$	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u> ; per diode	-	0.53	0.59	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u> ; per diode	-	0.49	0.56	V
		I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u> ; per diode	-	0.64	0.71	V
		I <sub>F</sub> = 20 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u> ; per diode	-	0.61	0.68	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 100 V; T <sub>j</sub> = 25 °C; <u>Fig. 7</u> ; <u>Fig. 8</u> ; per diode	-	-	50	μΑ
		V <sub>R</sub> = 100 V; T <sub>j</sub> = 125 °C; <u>Fig. 7</u> ; <u>Fig. 8</u> ; per diode	-	-	30	mA

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# **5. Pinning information**

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		A1
2	K	cathode		
3	A2	anode 2		K sym125
mb	К	mounting base; connected to cathode	TO-220E	

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package						
	Name	Description	Version				
WNS40H100C	TO-220E	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	TO-220E				

## 7. Limiting values

#### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	100	V
$V_{RWM}$	limiting crest working reverse voltage		-	100	V
$V_R$	limiting reverse voltage	DC	-	100	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 133 °C; square-wave pulse; per diode; Fig. 1; Fig. 2; Fig. 3	-	20	А
I <sub>O(AV)</sub>	average output current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 130 °C; square-wave pulse; both diodes conducting	-	40	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	-	380	А
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	-	418	А
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

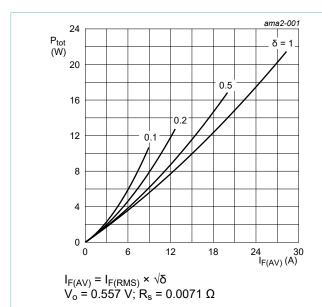


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode

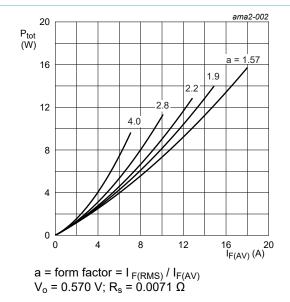


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

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### **Dual power Schottky diode**

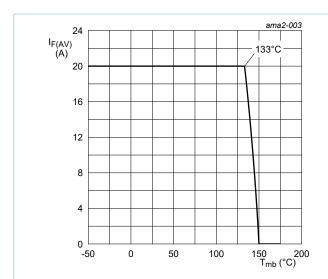


Fig. 3. Average forward current as a function of mounting base temperature; maximum values; per diode

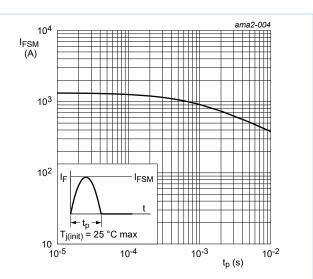


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

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## 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance	per diode; Fig. 5	-	-	1	K/W
	from junction to mounting base	both diodes conducting	-	-	0.6	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W

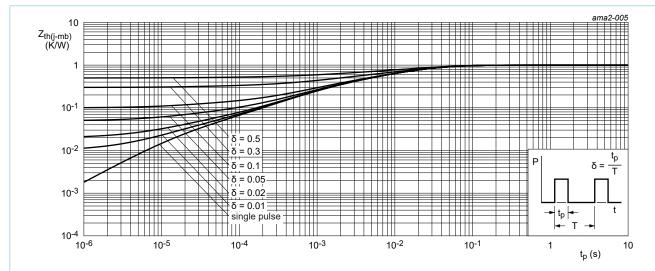


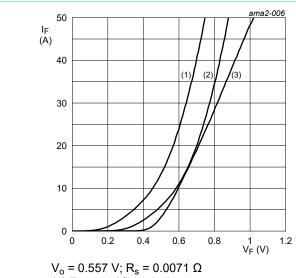
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values; per diode

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### 9. Characteristics

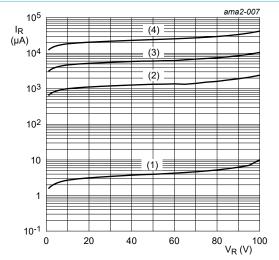
#### **Table 6. Characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static characte	Static characteristics							
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u> ; per diode		-	0.53	0.59	V	
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u> ; per diode		-	0.49	0.56	V	
	I <sub>F</sub> = 20	I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u> ; per diode		-	0.64	0.71	V	
		I <sub>F</sub> = 20 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u> ; per diode	-	0.61	0.68	V		
I <sub>R</sub>	reverse current	$V_R$ = 100 V; $T_j$ = 25 °C; <u>Fig. 7</u> ; <u>Fig. 8</u> ; per diode		-	-	50	μА	
		V <sub>R</sub> = 100 V; T <sub>j</sub> = 125 °C; <u>Fig. 7</u> ; <u>Fig. 8</u> ; per diode		-	-	30	mA	



<sup>(1)</sup> T<sub>i</sub> = 150 °C; typical values

Fig. 6. Forward current as a function of forward voltage; per diode



(1) T<sub>j</sub> = 25 °C; typical values

Fig. 7. Reverse leakage current as a function of reverse voltage; per diode; typical values

<sup>(2)</sup> T<sub>i</sub> = 150 °C; maximum values

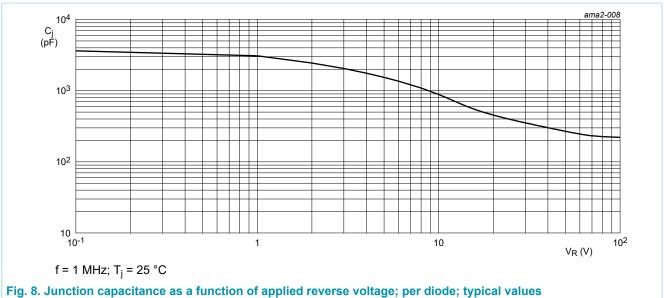
<sup>(3)</sup> T<sub>i</sub> = 25 °C; maximum values

<sup>(2)</sup>  $T_j = 100 \,^{\circ}\text{C}$ ; typical values (3)  $T_j = 125 \,^{\circ}\text{C}$ ; typical values

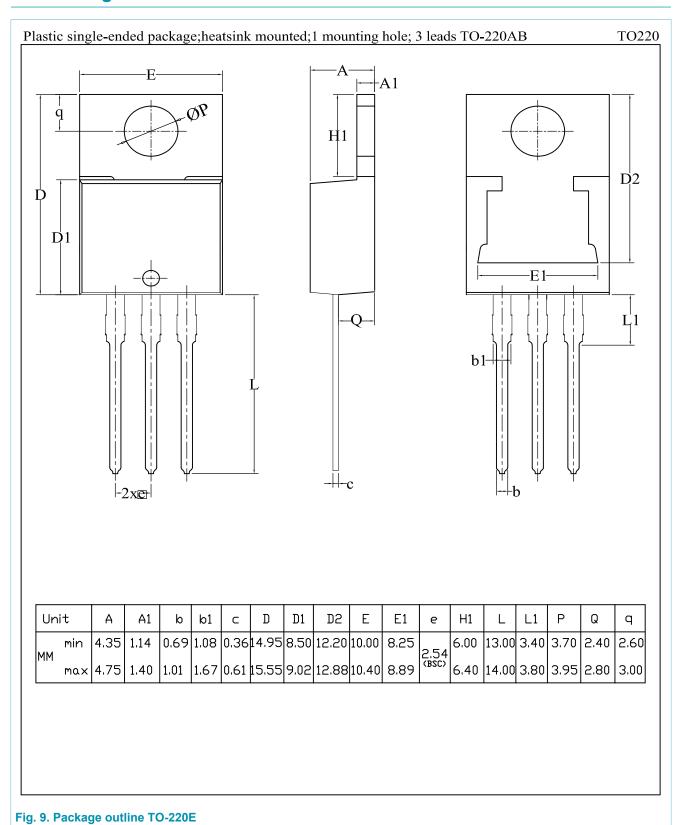
<sup>(4)</sup> T<sub>i</sub> = 150 °C; typical values

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## **Dual power Schottky diode**



## 10. Package outline



## 11. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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